ABSTRACT OF THE DISCLOSURE

METHOD FOR CLEANING SILICON WAFER

A method for cleaning a silicon wafer includes (S11) cleaning surfaces of a silicon wafer using an SC-1 cleaning solution according to standard clean 1; (S12) rinsing the surfaces of the silicon wafer, cleaned in the step S11, using deionized water; (S13) cleaning the surfaces of the silicon wafer, rinsed in the step S12, using a cleaning solution including hydrochloric acid, ozone water and deionized water; (S14) rinsing the surfaces of the silicon wafer, cleaned in the step S13, using deionized water; and (S15) drying the surfaces of the silicon wafer, rinsed in the step S14. A stable oxide film is formed on the surfaces of the silicon wafer using a material having a strong oxidizing ability while a cleaning process is performed. Therefore, a problem that as time passes, external impurities are attached to the surfaces of the silicon wafer can be solved by a simple and safe process.

FIG. 1

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